

**General Description**

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

cell density Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Product Summary**Application**

nd Synchronous Rectifier

Ordering Information:**Absolute Maximum Ratings** $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	40	A
	$I_{D@TC=75}$	30	A
	$I_{D@TC=100}$	25	A
Pulsed Drain Current	I_{DM}	120	A
Total Power Dissipation	$P_D@TC=25$	80	W
Total Power Dissipation	$P_D@TA=25$	2.5	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	30	mJ



Fig.7 Switching Time Measurement Circuit

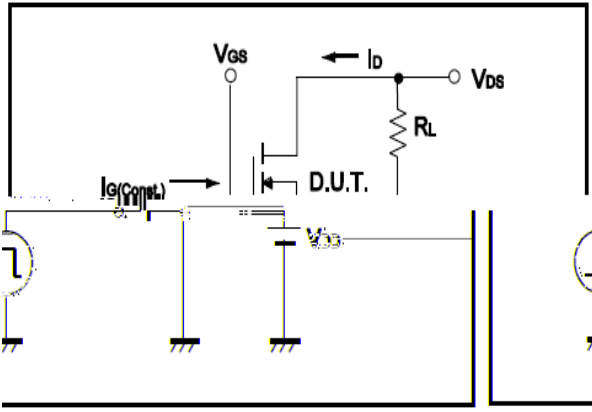


Fig.8 Gate Charge Waveform

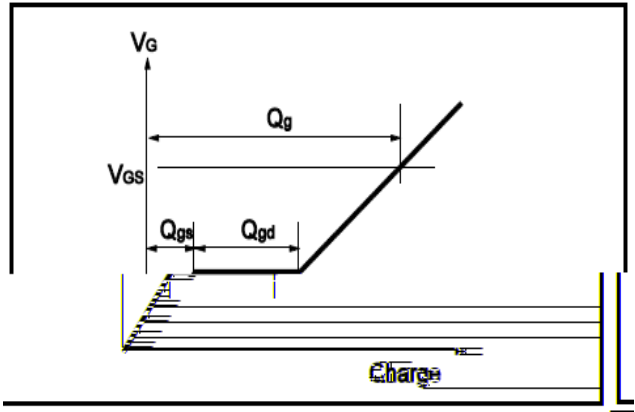


Fig.9 Switching Time Measurement Circuit

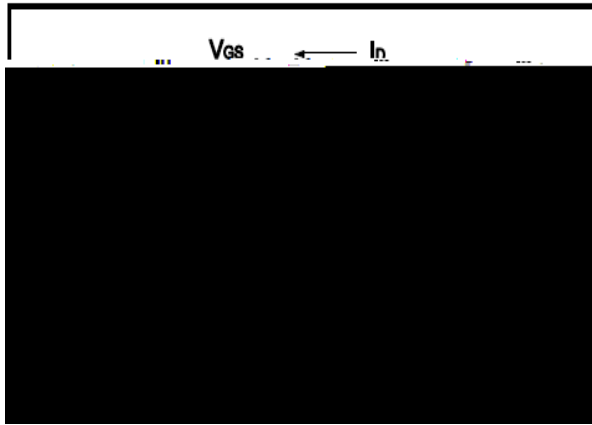


Fig.10 Gate Charge Waveform

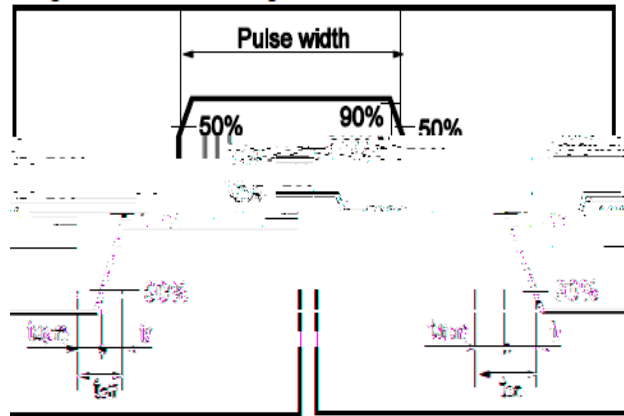


Fig.11 Avalanche Measurement Circuit

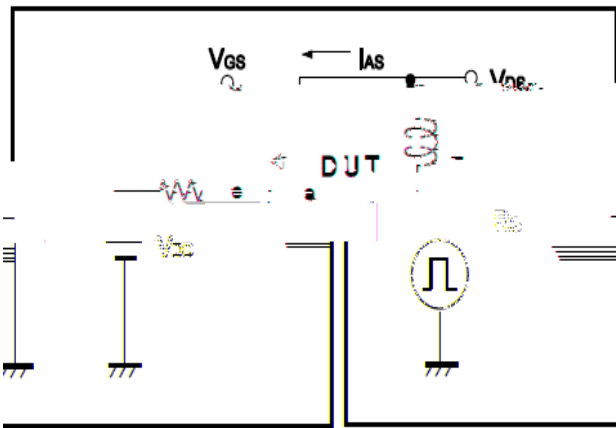
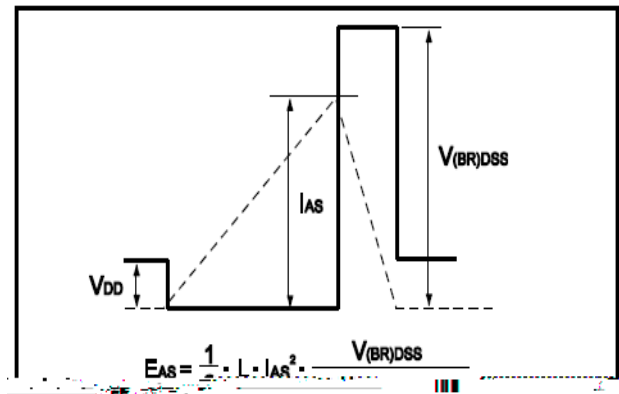


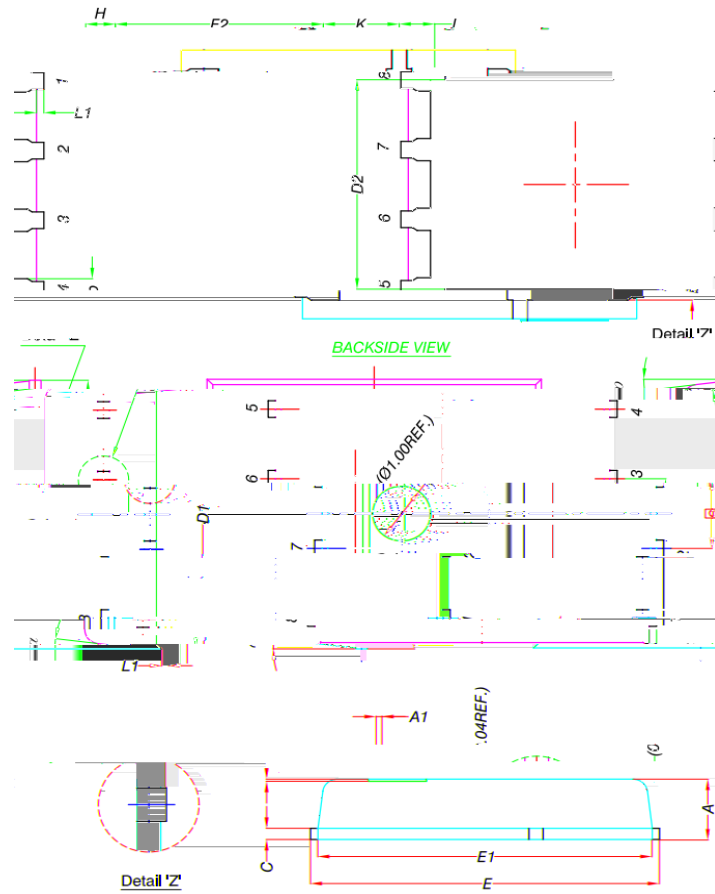
Fig.12 Avalanche Waveform





Dimensions DFN5x6

Unit mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96

